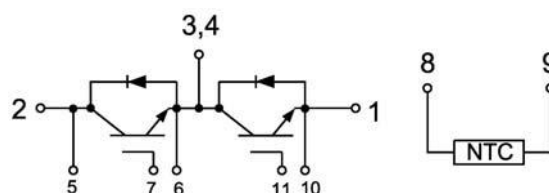


JGT600HF120G9H

IGBT Module

Features:

- Trench & Field Stop IGBT
- Short Circuit Rated > 10 μ s
- Low Switching Loss
- 100% RBSOA Tested (2X I_c)
- Low Stray Inductance
- Copper Wire Bonding on Power Terminal
- Lead Free, Compliant with RoHS Requirement



Applications:

- Hybrid Electrical Vehicles(H)EV
- Automotive Applications
- Commercial Agriculture Vehicles
- Motor Drives

IGBT, Inverter

Maximum Rated Values($T_c=25^\circ\text{C}$ unless otherwise specified)

V_{CES}	Collector-Emitter Blocking Voltage		1200	V
V_{GES}	Gate-Emitter Voltage		± 20	V
I_C	Continuous Collector Current	$T_c=100^\circ\text{C}$	600	A
		$T_c=25^\circ\text{C}$	1160	A
I_{CM}	Peak Collector Current Repetitive	$T_J=175^\circ\text{C}$	1200	A
t_{SC}	Short Circuit Withstand Time		>10	μs
P_D	Maximum Power Dissipation (IGBT)	$T_c=25^\circ\text{C}$ $T_{Jmax}=175^\circ\text{C}$	3950	W

Electrical Characteristics of IGBT ($T_C=25^\circ\text{C}$ unless otherwise specified)
Static Characteristics

Symbol	Description	Conditions	Min	Typ	Max	Unit
$V_{GE(th)}$	Gate-Emitter Threshold Voltage	$I_C=10\text{mA}$, $V_{CE}=V_{GE}$	5.0	5.5	6.8	V
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	$I_C=60\text{0A}$, $V_{GE}=1\text{5V}$	$T_J=25^\circ\text{C}$	1.70	1.95	V
			$T_J=125^\circ\text{C}$	1.90		V
			$T_J=150^\circ\text{C}$	2.00		V
I_{CES}	Collector-Emitter Leakage Current	$V_{GE}=0\text{V}$, $V_{CE}=V_{CES}$, $T_J=25^\circ\text{C}$			1	mA
I_{GES}	Gate-Emitter Leakage Current	$V_{GE}=\pm 20\text{V}$, $V_{CE}=0\text{V}$, $T_J=25^\circ\text{C}$			800	nA
C_{ies}	Input Capacitance	$V_{CE}=25\text{V}$, $V_{GE}=0\text{V}$, $f=1\text{MHz}$		49.26		nF
C_{oes}	Output Capacitance			3.67		nF
C_{res}	Reverse Transfer Capacitance			1.85		nF

Switching Characteristics

$t_{d(on)}$	Turn-on Delay Time	$V_{CC}=600\text{V}$, $I_C=600\text{A}$, $R_{Gon}=1\Omega$, $V_{GE}=\pm 15\text{V}$, Inductive Load	$T_J=25^\circ\text{C}$	0.55		μs
			$T_J=125^\circ\text{C}$	0.56		
			$T_J=150^\circ\text{C}$	0.56		
t_r	Rise Time		$T_J=25^\circ\text{C}$	0.22		μs
			$T_J=125^\circ\text{C}$	0.22		
			$T_J=150^\circ\text{C}$	0.23		
$t_{d(off)}$	Turn-off Delay Time		$T_J=25^\circ\text{C}$	0.54		μs
			$T_J=125^\circ\text{C}$	0.57		
			$T_J=150^\circ\text{C}$	0.57		
t_f	Fall Time	$T_J=25^\circ\text{C}$	0.14		μs	
		$T_J=125^\circ\text{C}$	0.18			
		$T_J=150^\circ\text{C}$	0.19			
E_{on}	Turn-on Switching Loss	$V_{CC}=600\text{V}$, $I_C=600\text{A}$, $R_{Gon}=1\Omega$, $V_{GE}=\pm 15\text{V}$, $di/dt=2120\text{A}/\mu\text{s}$ ($T_J=150^\circ\text{C}$) Inductive Load	$T_J=25^\circ\text{C}$	49.0		mJ
		$T_J=125^\circ\text{C}$	75.8			
		$T_J=150^\circ\text{C}$	81.2			

E _{off}	Turn-off Switching Loss	V _{CC} =600V, I _C =600A, R _{Goff} =1Ω, V _{GE} = ±15V, du/dt=2600V/μs (T _J =150°C) Inductive Load	T _J =25°C	81.5	mJ
			T _J =125°C	96.1	
			T _J =150°C	100.1	
Q _g	Total Gate Charge	V _{GE} =+15V...-15V	T _J =25°C	3.36	μC
R _{g internal}	Internal Gate Resistance		T _J =25°C	1.1	Ω
RBSO A	I _C =1200A, V _{CC} =1050V, V _p =1200V, R _{Goff} = 1Ω, V _{GE} =+15V to 0V, T _J =150°C	Trapezoid			
SCSO A	V _{CC} =600V, V _{GE} =15V, T _J =150°C	10			μs
R _{θJC}	IGBT Thermal Resistance: Junction-To-Case(per leg)			0.038	°C /W

Maximum Rated Values of Diode (T_C=25°C unless otherwise specified)

V _{RRM}	Repetitive Peak Reverse Voltage	1200	V
I _F	Diode Continuous Forward Current	600	A
I _{FM}	Diode Maximum Forward Current	1200	A

Electrical Characteristics of Diode (T_C=25°C unless otherwise specified)

Symbol	Description	Conditions	Min	Typ	Max	Unit
V _{FM}	Forward Voltage	I _F =600A	T _J =25°C	1.80	2.00	V
			T _J =125°C	1.90		
			T _J =150°C	1.90		
t _{rr}	Reverse Recovery Time	I _F =600A, -diF/dt=2270A/μs(T _J =150°C), V _R =600V, V _{GE} =-15V	T _J =25°C	0.37		μs
			T _J =125°C	0.58		
			T _J =150°C	0.65		
I _{rr}	Peak Reverse Recovery Current	I _F =600A, -diF/dt=2270A/μs(T _J =150°C), V _R =600V, V _{GE} =-15V	T _J =25°C	238		A
			T _J =125°C	294		
			T _J =150°C	306		

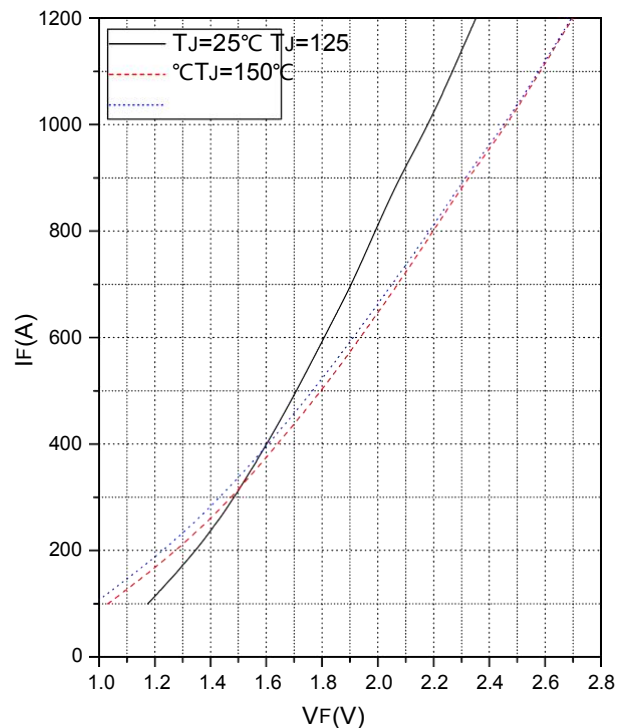
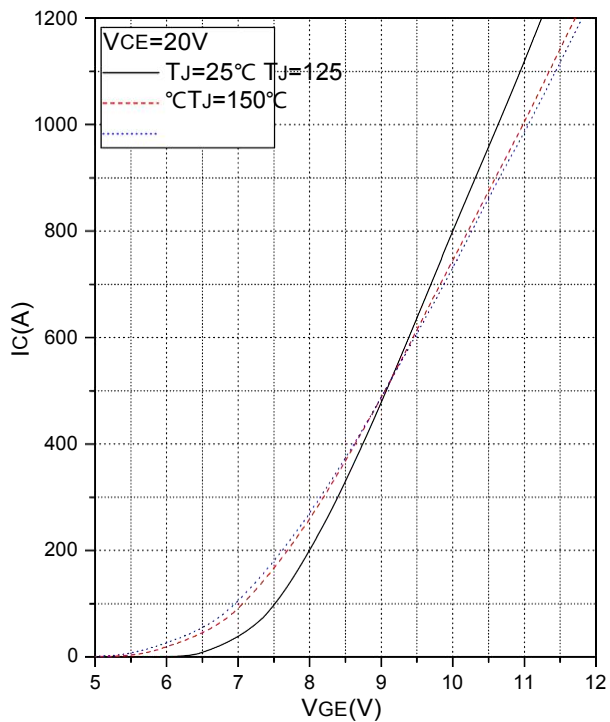
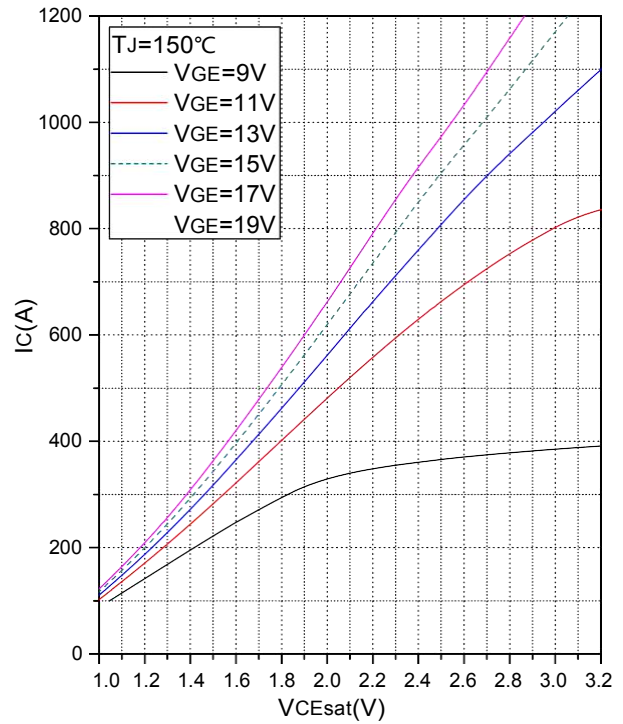
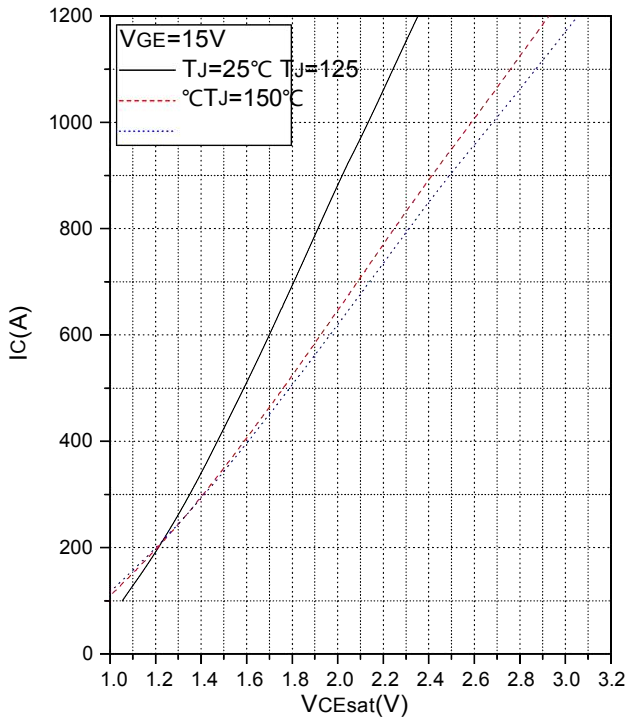
Q _{rr}	Reverse Recovery Charge	I _F =600A, -diF/dt=2270A/μs(T _J =150°C), V _R =600V, V _{GE} =-15V	T _J =25°C		52.3		μC
			T _J =125°C		96.1		
			T _J =150°C		110.6		
E _{rec}	Reverse Recovery Energy		T _J =25°C		22.0		mJ
			T _J =125°C		38.3		
			T _J =150°C		44.6		
R _{θJC}	Diode Thermal Resistance: Junction-To-Case (per leg)				0.064		°C /W

Internal NTC-Thermistor Characteristics

R ₂₅	T _C =25°C	5		kΩ
ΔR/R	T _C =100°C, R ₁₀₀ =481Ω		±5	%
P ₂₅	T _C =25°C	50		mW
B _{25/50}	R ₂ =R ₂₅ exp[B _{25/50} (1/T ₂ -1/(298.15K))]	3380		K
B _{25/80}	R ₂ =R ₂₅ exp[B _{25/80} (1/T ₂ -1/(298.15K))]	3440		K

Module

Symb ol	Description		Min	Typ	Max	Unit
V _{iso}	Isolation Voltage (All Terminals Shorted)	f = 50Hz, 1minute	2500			V
L _{SCE}	Stray Inductance Module			20		nH
T _J	Maximum Junction Temperature				175	°C
T _{JOP}	Maximum Operating Junction Temperature Range		-40		+150	°C
T _{stg}	Storage Temperature		-40		+125	°C
CTI	Comparative Tracking Index		200			
R _{θCS}	Case-To-Sink Thermally (Conductive Grease Applied)			0.02		°C /W
M	Power Terminals Screw:M5		3.0		5.0	N·m
M	Mounting Screw:M6		4.0		6.0	N·m
G	Weight			330		g



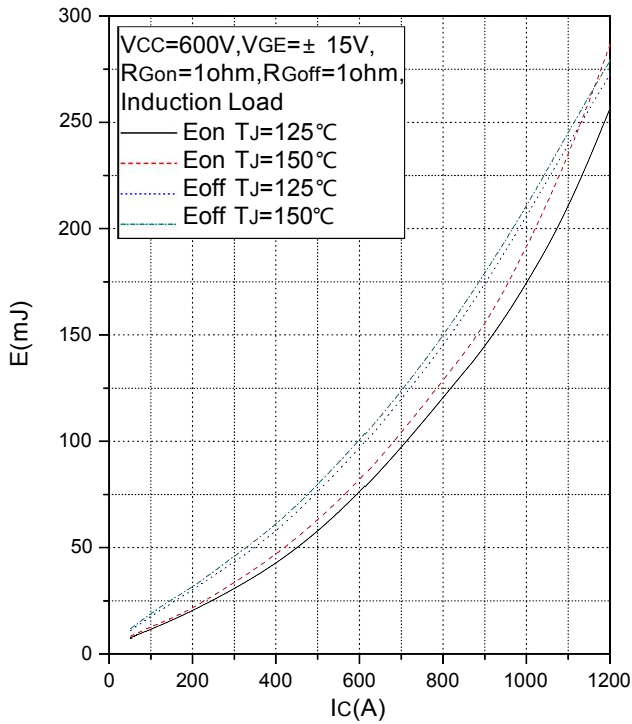


Fig.5 Typical Switching Loss vs. Collector Current

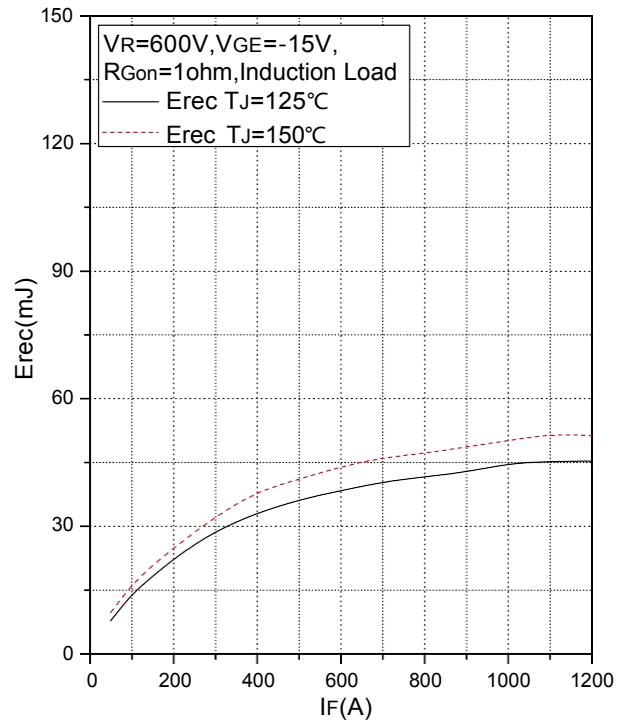


Fig.6 Typical Switching Loss vs. Forward Current

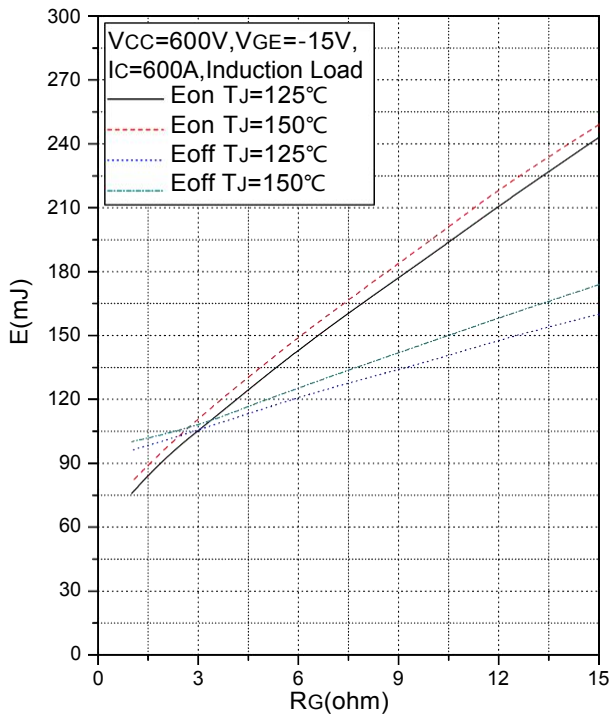


Fig.7 Typical Switching Loss vs. Gate Resistance

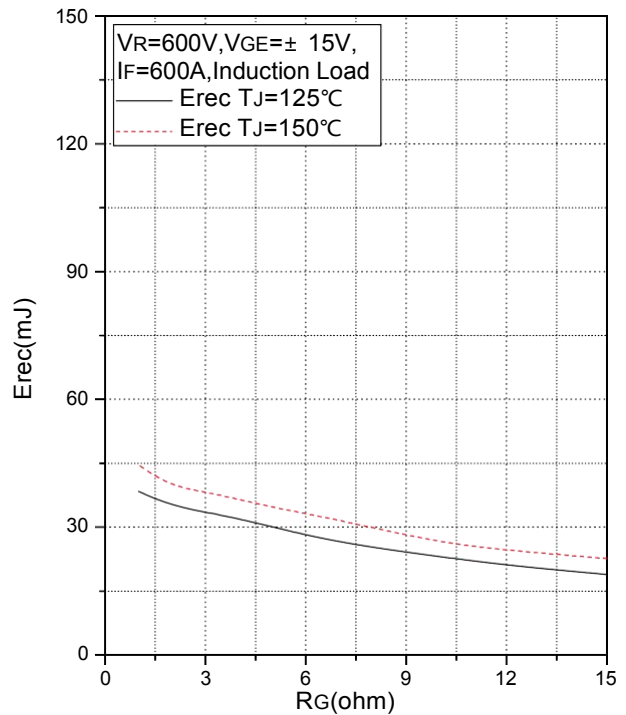


Fig.8 Typical Switching Loss vs. Gate Resistance

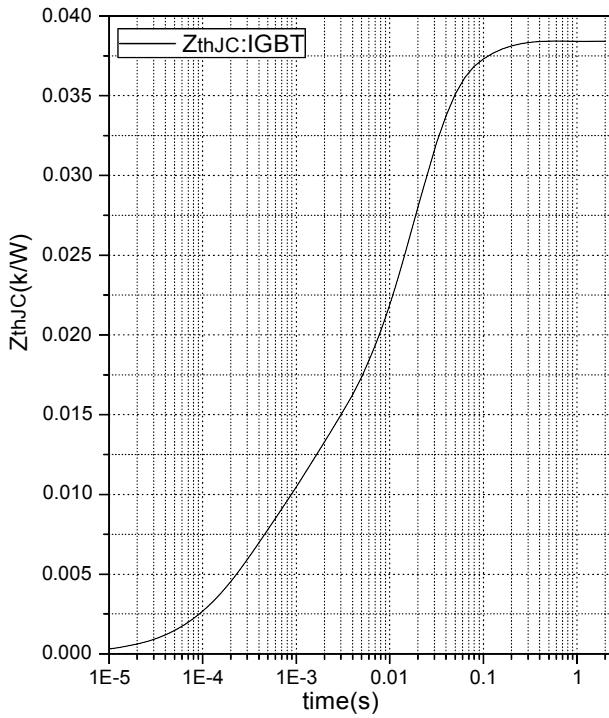


Fig.9 Transient Thermal Impedance (IGBT)

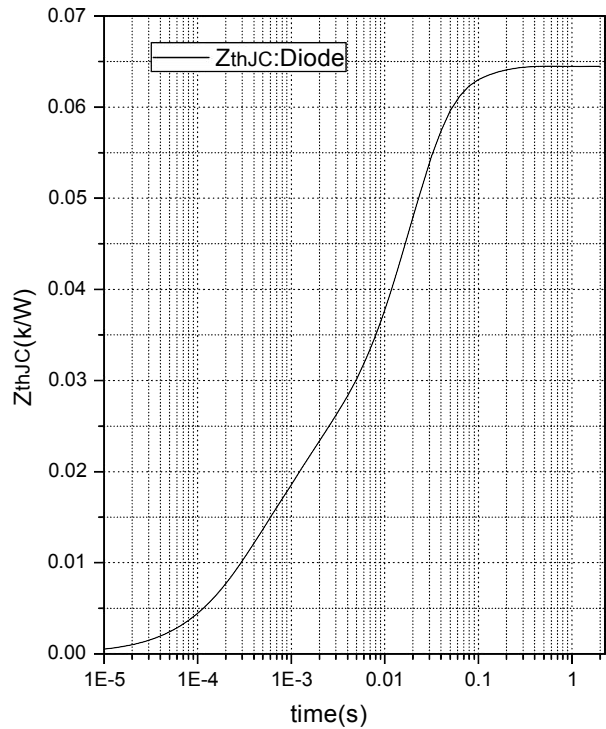


Fig.10 Transient Thermal Impedance (Diode)

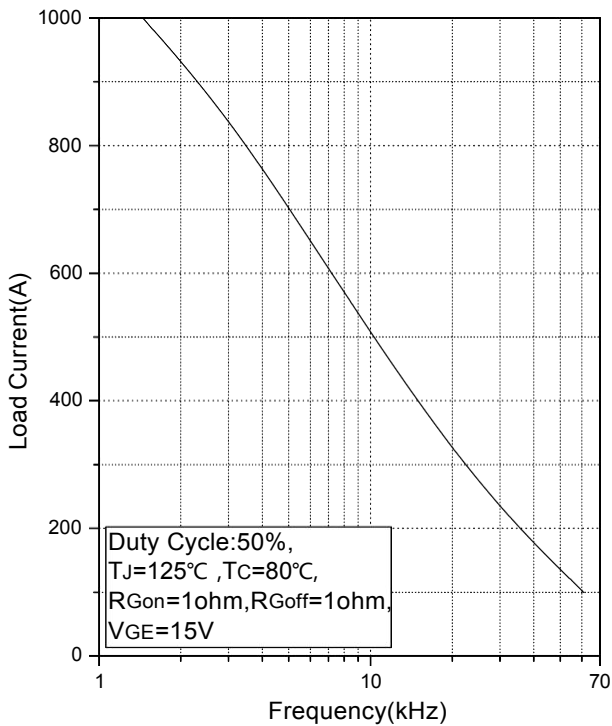


Fig.11 Typical Load Current vs. Frequency

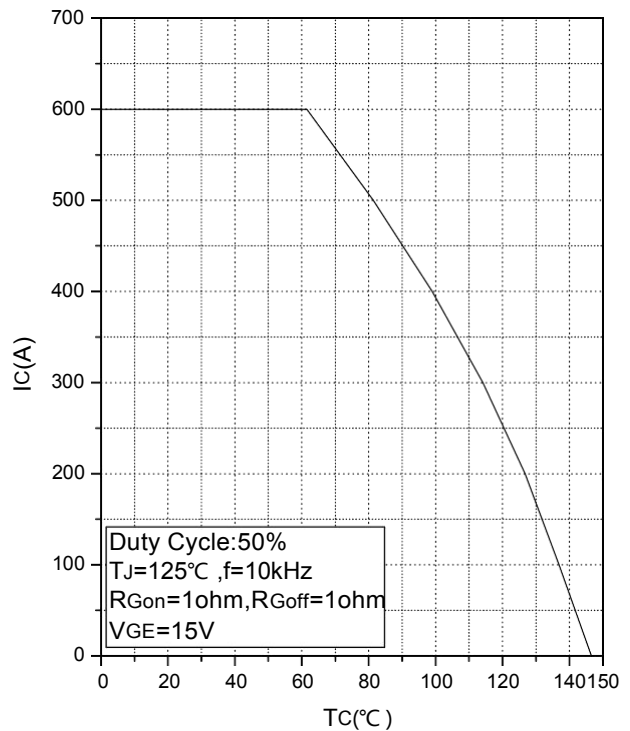


Fig.12 Rated Current vs. Temperature

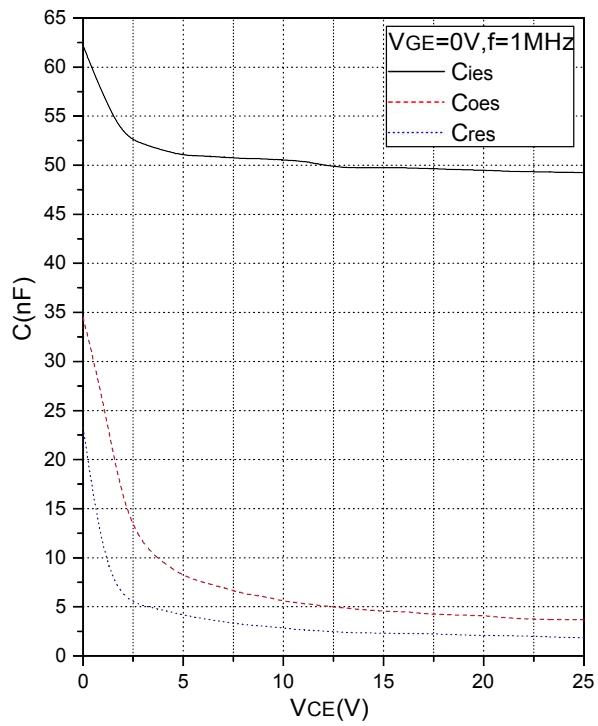


Fig.13 Capacitance Characteristics

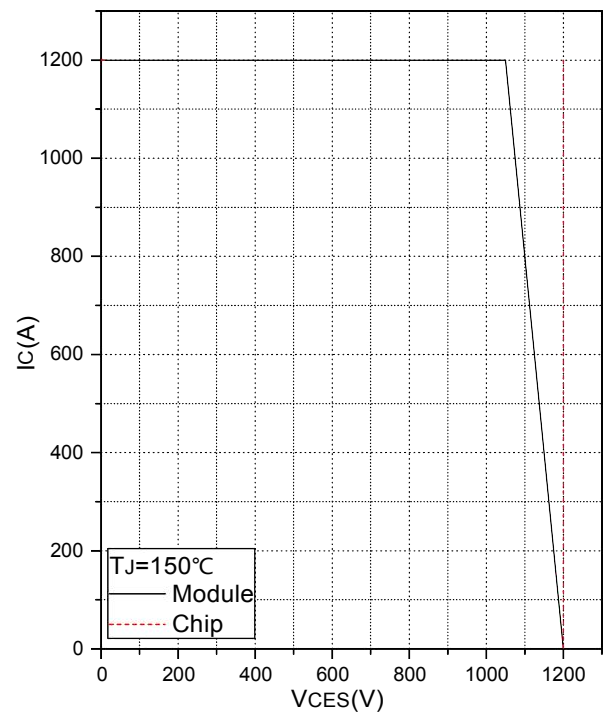


Fig.14 Reverse Bias Safe Operation Area (RBSOA)

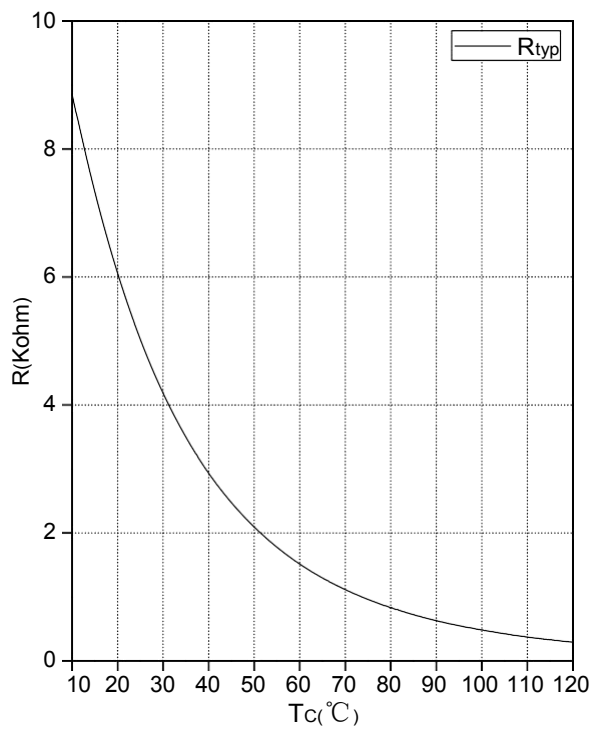
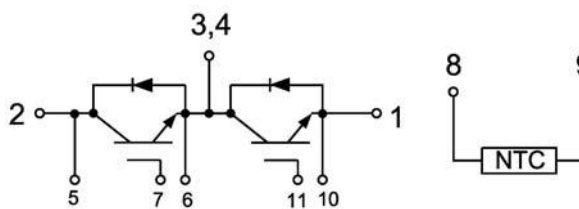
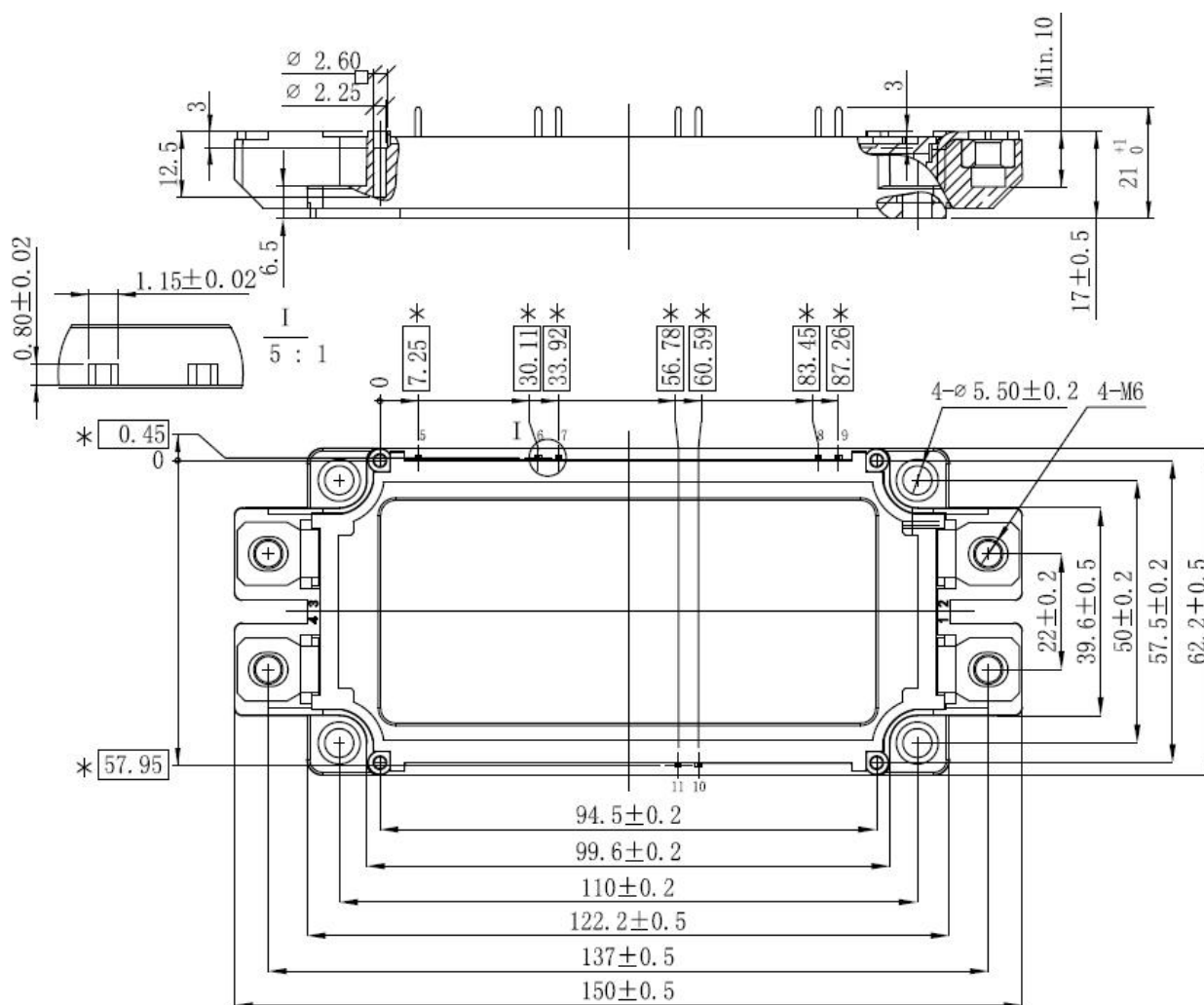


Fig.15 NTC Temperature Characteristics

Internal Circuit:



Package Outline (Unit: mm):





Date	Revision	Notes
04/18/2022	01	Initial Release